

OptiMOS[®] 2 Power-MOSFET
Features

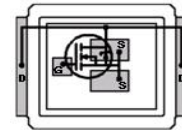
- Pb-free plating; RoHS compliant
- Dual sided cooling
- Low profile (<0.7 mm)
- 100% avalanche tested
- Qualified for consumer level application
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Very low on-resistance $R_{DS(on)}$
- Optimized for high switching frequency DC/DC converter
- Low parasitic inductance
- Compatible with DirectFET[®] package MX footprint and outline ¹⁾

Product Summary

V_{DS}	30	V
$R_{DS(on),max}$	2.4	m Ω
I_D	145	A

MG-WDSON-2


Type	Package	Outline	Marking
BSB024N03LX G	MG-WDSON-2	MX	0603


Maximum ratings, at $T_j=25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$V_{GS}=10\text{ V}, T_C=25\text{ }^\circ\text{C}$	145	A
		$V_{GS}=10\text{ V}, T_C=100\text{ }^\circ\text{C}$	92	
		$V_{GS}=10\text{ V}, T_A=25\text{ }^\circ\text{C}, R_{thJA}=45\text{ K/W}^2$	27	
Pulsed drain current ³⁾	$I_{D,pulse}$	$T_C=25\text{ }^\circ\text{C}$	400	
Avalanche current, single pulse ⁴⁾	I_{AS}	$T_C=25\text{ }^\circ\text{C}$	50	
Avalanche energy, single pulse	E_{AS}	$I_D=50\text{ A}, R_{GS}=25\text{ }\Omega$	220	mJ
Gate source voltage	V_{GS}		± 20	V

¹⁾ DirectFET[®] is a trademark of International Rectifier Corporation

BSB024N03LX G uses DirectFET[®] technology licensed from International Rectifier Corporation

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Power dissipation	P_{tot}	$T_C=25\text{ °C}$	78	W
		$T_A=25\text{ °C}$, $R_{\text{thJA}}=45\text{ K/W}^2)$	2.8	
Operating and storage temperature	T_j, T_{stg}		-40 ... 150	°C
IEC climatic category; DIN IEC 68-1			55/150/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		-	-	1.6	K/W
Device on PCB	R_{thJA}	6 cm ² cooling area ²⁾	-	-	45	

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified
Static characteristics

Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}}=0\text{ V}$, $I_{\text{D}}=1\text{ mA}$	30	-	-	V
Gate threshold voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}$, $I_{\text{D}}=250\text{ }\mu\text{A}$	1	-	2.2	
Zero gate voltage drain current	I_{DSS}	$V_{\text{DS}}=30\text{ V}$, $V_{\text{GS}}=0\text{ V}$, $T_j=25\text{ °C}$	-	0.1	1	μA
		$V_{\text{DS}}=30\text{ V}$, $V_{\text{GS}}=0\text{ V}$, $T_j=125\text{ °C}$	-	10	100	
Gate-source leakage current	I_{GSS}	$V_{\text{GS}}=20\text{ V}$, $V_{\text{DS}}=0\text{ V}$	-	10	100	nA
Drain-source on-state resistance	$R_{\text{DS(on)}}$	$V_{\text{GS}}=4.5\text{ V}$, $I_{\text{D}}=25\text{ A}$	-	3.4	4.2	m Ω
		$V_{\text{GS}}=10\text{ V}$, $I_{\text{D}}=30\text{ A}$	-	2.0	2.4	
Gate resistance	R_{G}		-	0.6	-	Ω
Transconductance	g_{fs}	$ V_{\text{DS}} >2 I_{\text{D}} R_{\text{DS(on)max}}$, $I_{\text{D}}=30\text{ A}$	50	100	-	S

²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

³⁾ See figure 3 for more detailed information

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=15\text{ V},$ $f=1\text{ MHz}$	-	4900	-	pF
Output capacitance	C_{oss}		-	1700	-	
Reverse transfer capacitance	C_{rss}		-	220	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=15\text{ V}, V_{GS}=10\text{ V},$ $I_D=30\text{ A}, R_G=1.6\ \Omega$	-	8.4	-	ns
Rise time	t_r		-	7.0	-	
Turn-off delay time	$t_{d(off)}$		-	35	-	
Fall time	t_f		-	5.6	-	

Gate Charge Characteristics⁵⁾

Gate to source charge	Q_{gs}	$V_{DD}=15\text{ V}, I_D=30\text{ A},$ $V_{GS}=0\text{ to }4.5\text{ V}$	-	14	-	nC
Gate charge at threshold	$Q_{g(th)}$		-	7.9	-	
Gate to drain charge	Q_{gd}		-	9.6	-	
Switching charge	Q_{sw}		-	16	-	
Gate charge total	Q_g		-	35	-	
Gate plateau voltage	$V_{plateau}$		-	2.9	-	V
Gate charge total	Q_g	$V_{DD}=15\text{ V}, I_D=30\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	72	-	nC
Gate charge total, sync. FET	$Q_{g(sync)}$	$V_{DS}=0.1\text{ V},$ $V_{GS}=0\text{ to }4.5\text{ V}$	-	30	-	
Output charge	Q_{oss}	$V_{DD}=15\text{ V}, V_{GS}=0\text{ V}$	-	39	-	

Reverse Diode

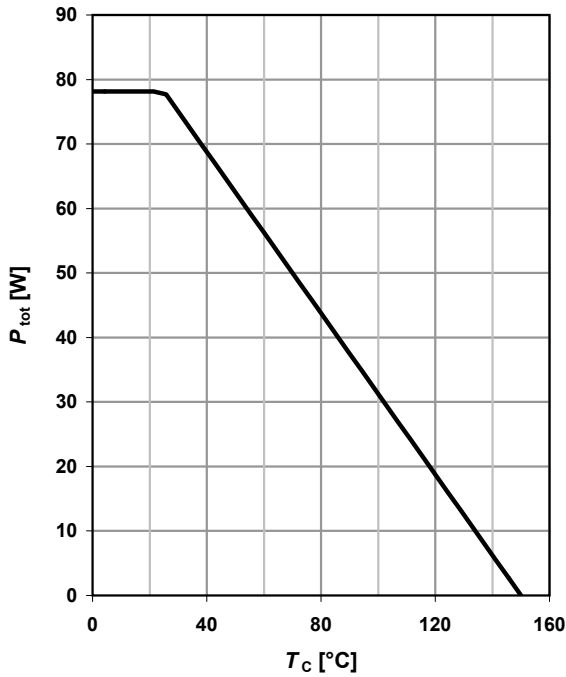
Diode continuous forward current	I_S	$T_C=25\text{ }^\circ\text{C}$	-	-	78	A
Diode pulse current	$I_{S,pulse}$		-	-	400	
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=30\text{ A},$ $T_j=25\text{ }^\circ\text{C}$	-	0.79	-	V
Reverse recovery charge	Q_{rr}	$V_R=15\text{ V}, I_F=I_S,$ $di_F/dt=400\text{ A}/\mu\text{s}$	-	-	50	nC

⁴⁾ See figure 13 for more detailed information

⁵⁾ See figure 16 for gate charge parameter definition

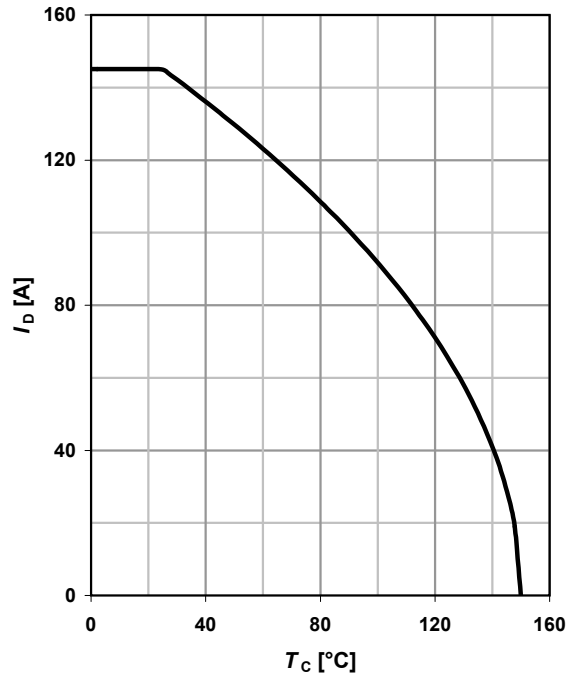
1 Power dissipation

$P_{tot}=f(T_C)$



2 Drain current

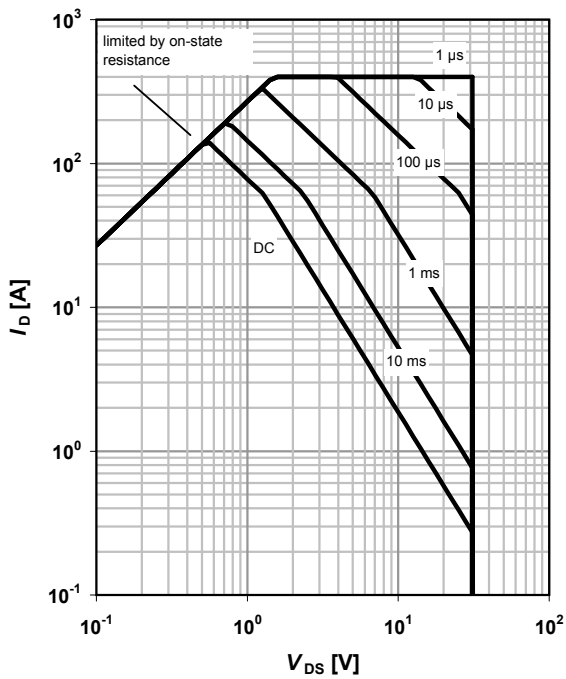
$I_D=f(T_C); V_{GS} \geq 10\text{ V}$



3 Safe operating area

$I_D=f(V_{DS}); T_C=25\text{ °C}; D=0$

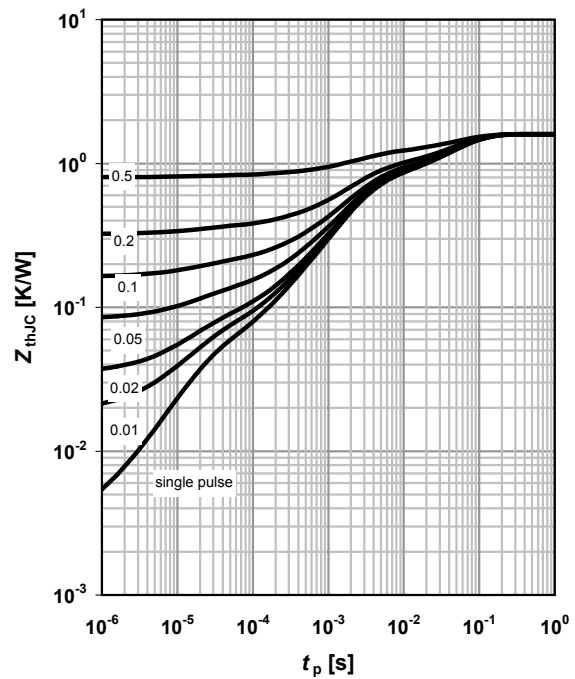
parameter: t_p



4 Max. transient thermal impedance

$Z_{thJC}=f(t_p)$

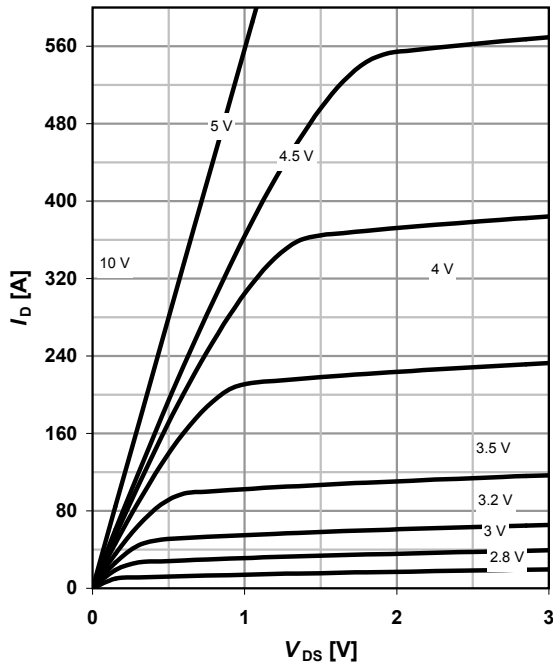
parameter: $D=t_p/T$



5 Typ. output characteristics

$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$

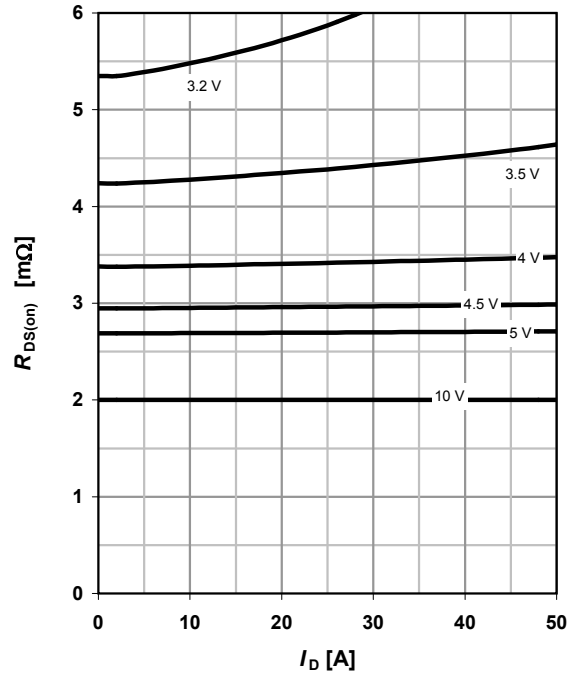
parameter: V_{GS}



6 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$

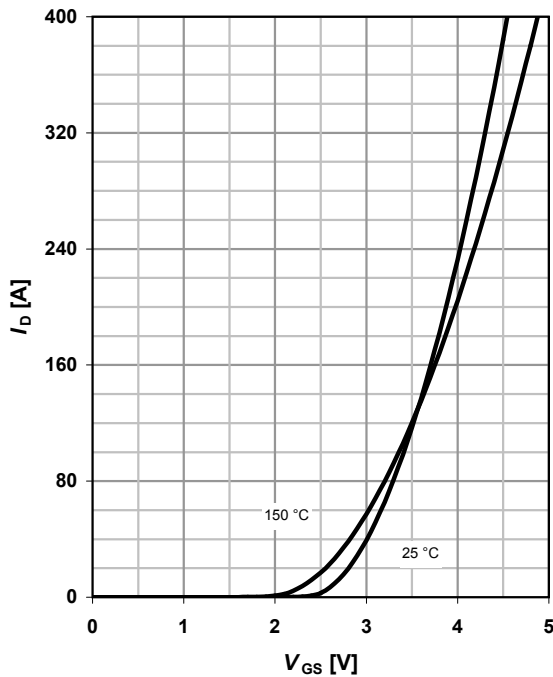
parameter: V_{GS}



7 Typ. transfer characteristics

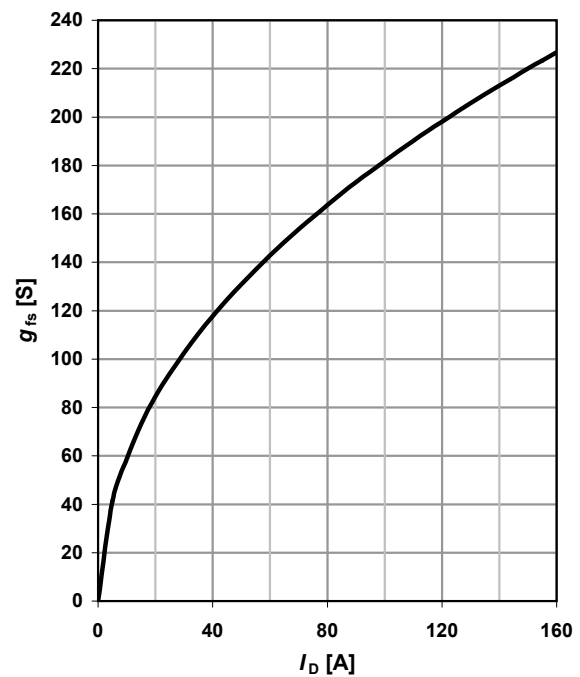
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter: T_j



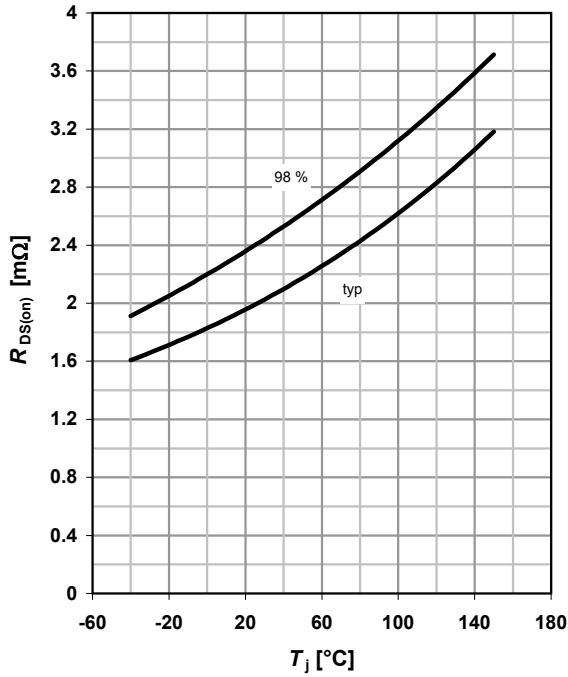
8 Typ. forward transconductance

$g_{fs} = f(I_D); T_j = 25\text{ }^\circ\text{C}$



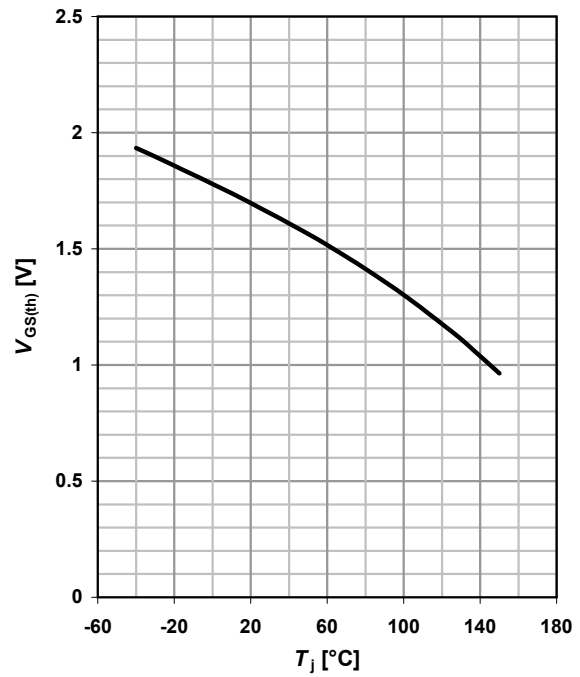
9 Drain-source on-state resistance

$R_{DS(on)} = f(T_j); I_D = 30 \text{ A}; V_{GS} = 10 \text{ V}$



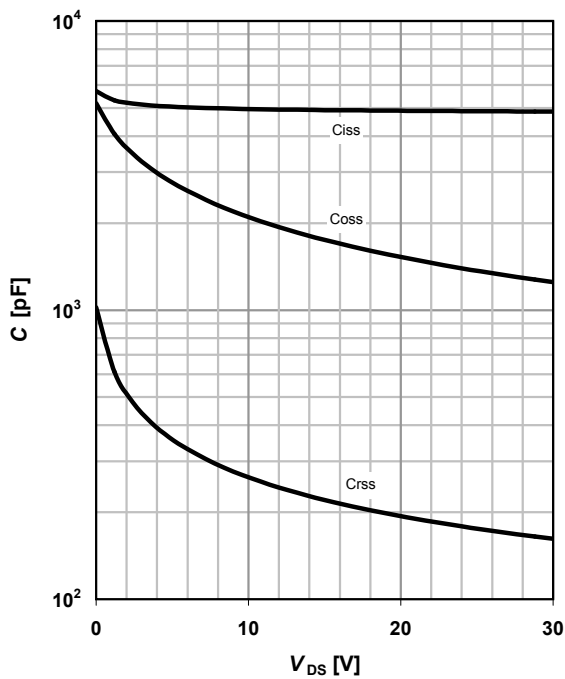
10 Typ. gate threshold voltage

$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}; I_D = 250 \mu\text{A}$



11 Typ. capacitances

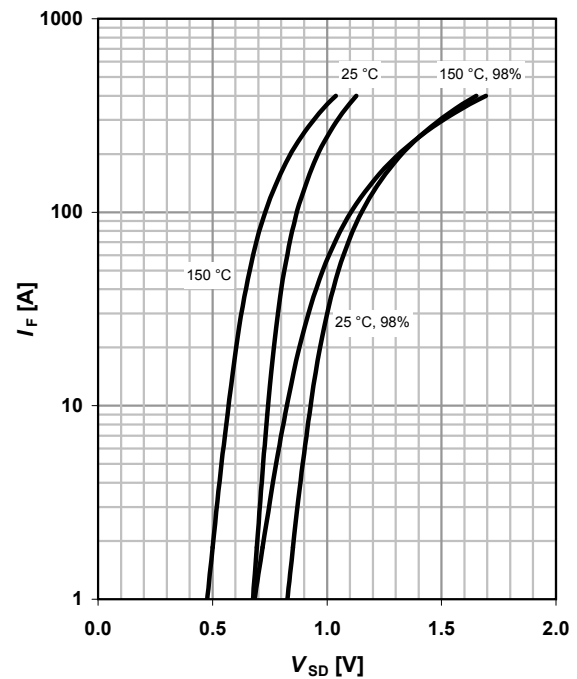
$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



12 Forward characteristics of reverse diode

$I_F = f(V_{SD})$

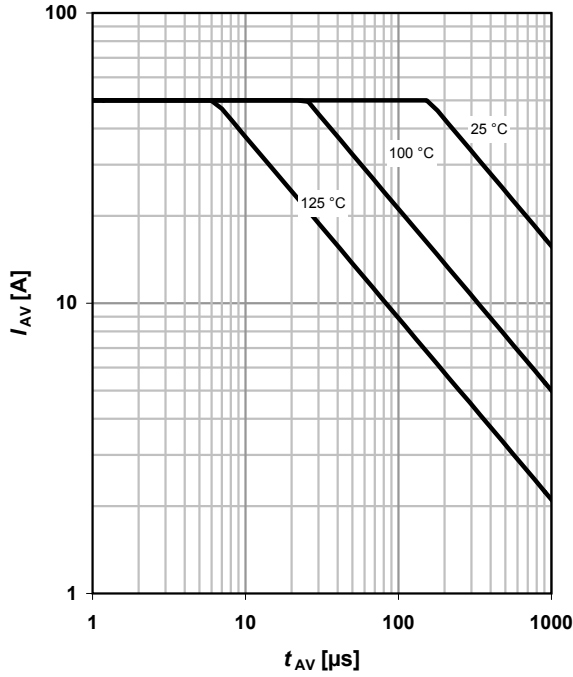
parameter: T_j



13 Avalanche characteristics

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

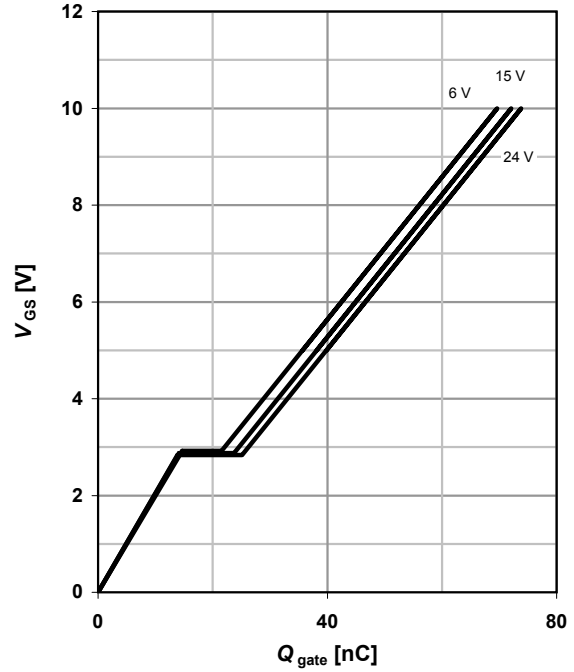
parameter: $T_{j(start)}$



14 Typ. gate charge

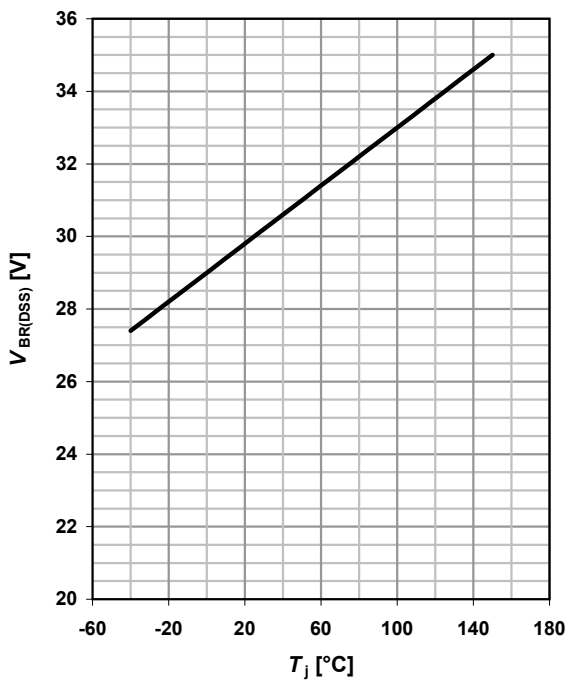
$V_{GS}=f(Q_{gate}); I_D=30 \text{ A pulsed}$

parameter: V_{DD}



15 Drain-source breakdown voltage

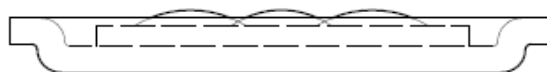
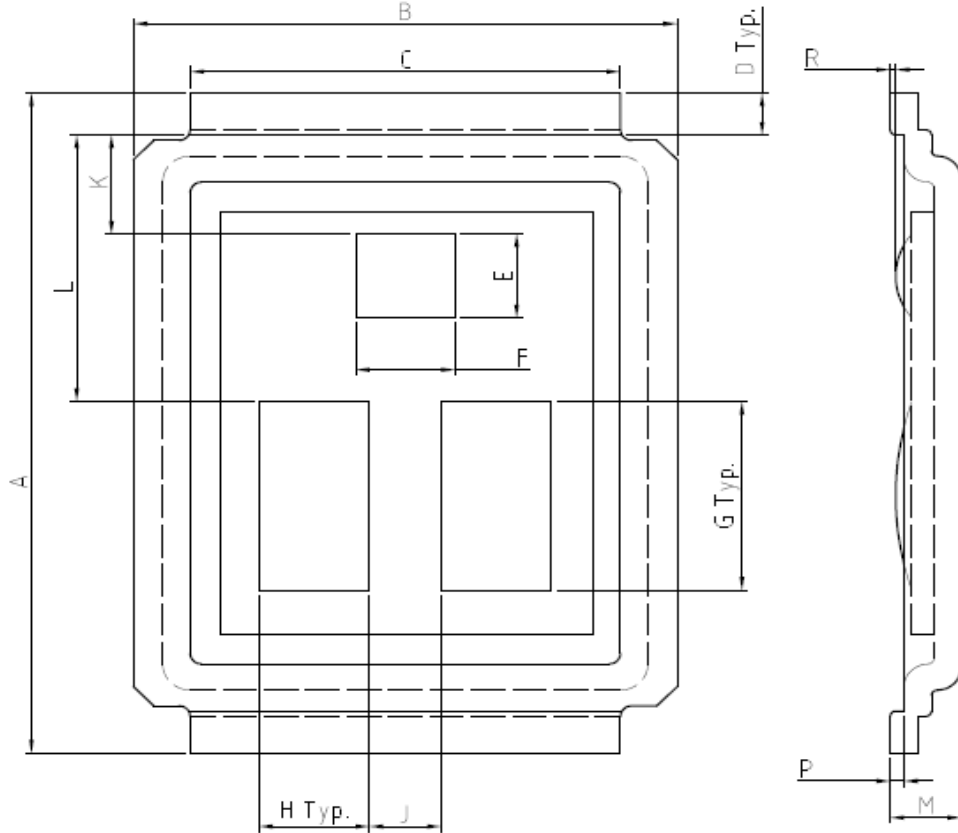
$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$



16 Gate charge waveforms



MG-WDSO-2



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	6,25	6,35	0,246	0,250
B	4,80	5,05	0,189	0,199
C	3,85	3,95	0,152	0,156
D	0,35	0,45	0,014	0,018
E	0,78	0,82	0,031	0,032
F	0,88	0,92	0,035	0,036
G	1,78	1,82	0,070	0,072
H	0,98	1,02	0,039	0,040
J	0,63	0,67	0,025	0,026
K	0,88	1,01	0,035	0,039
L	2,46	2,63	0,097	0,104
M	0,62	0,68	0,024	0,027
R	0,02	0,08	0,001	0,003
P	0,08	0,17	0,003	0,007

DOCUMENT NO.
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SCALE

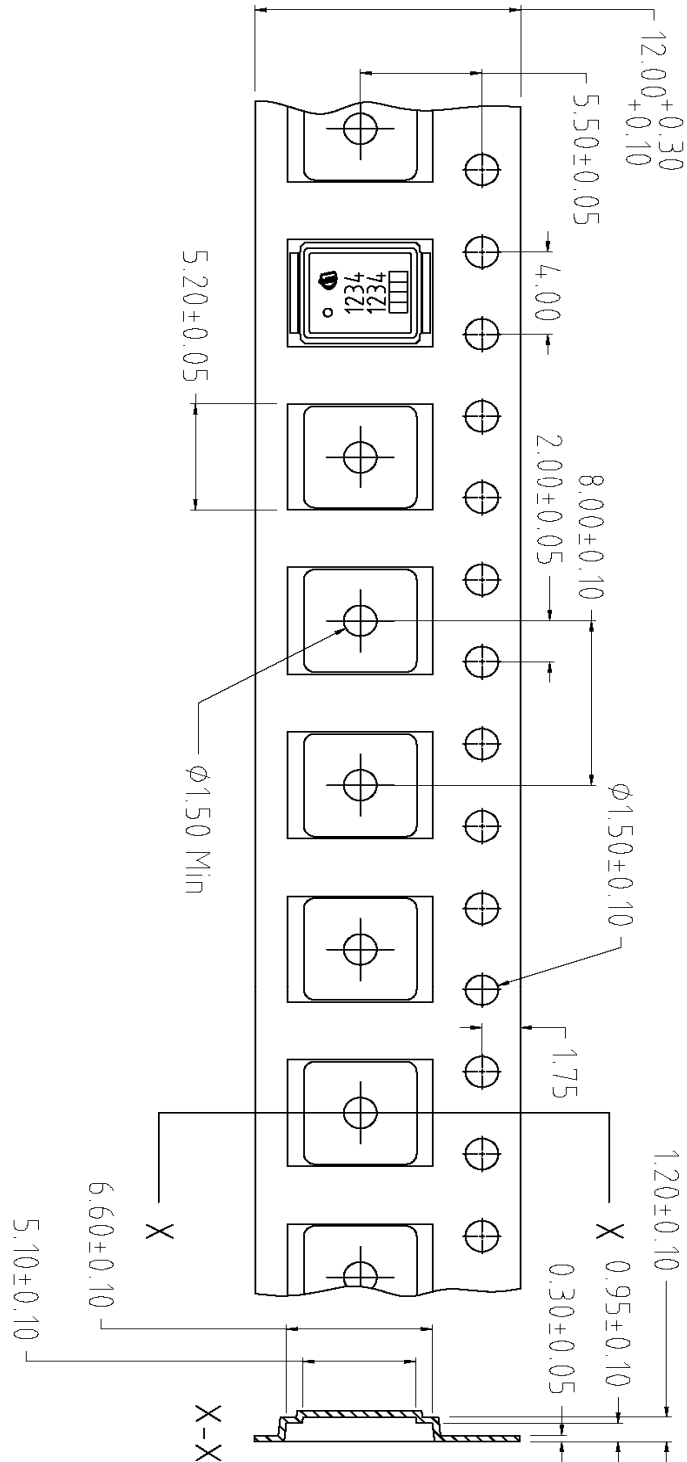
EUROPEAN PROJECTION

ISSUE DATE
10-10-2007

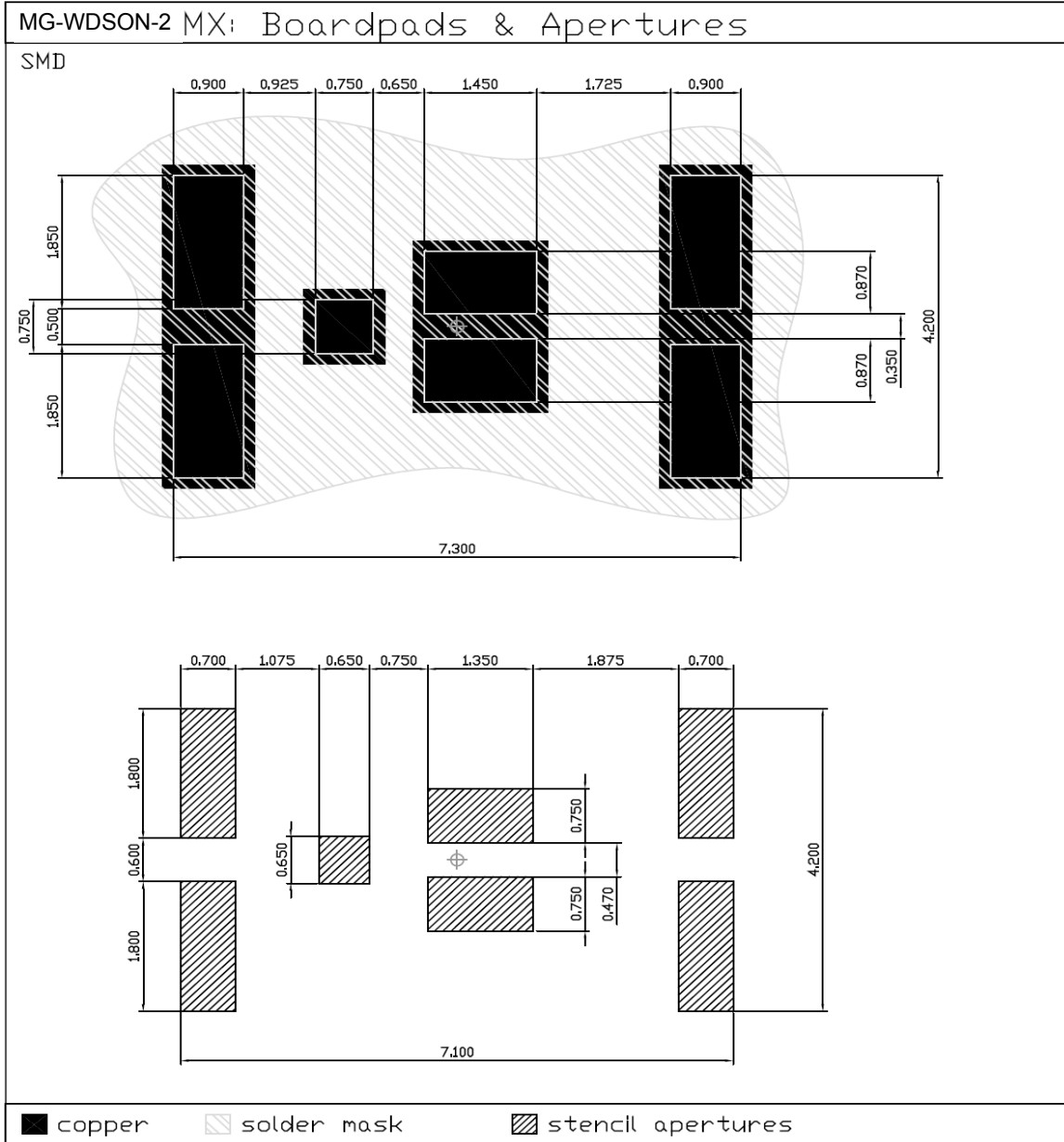
REVISION
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Package Outline

MG-WDSO-2



Dimensions in mm



Dimensions in mm

Reccomended stencil thickness 150 μ m

0.6

Published by

Infineon Technologies AG
81726 Munich, Germany
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